MGBR20L60 Preliminary DIODE

MOS GATED BARRIER RECTIFIER

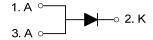
■ DESCRIPTION

The UT C MGBR20L60 is a surface mount mos gatedbarrie rectifier,it uses UTC's advanced technology to provi decustomers withlow forward voltage drop and high switching speed, etc.

■ FEATURES

- * Low forward voltage drop
- * High switching speed

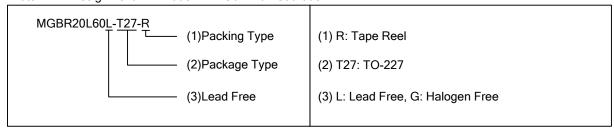
■ SYMBOL



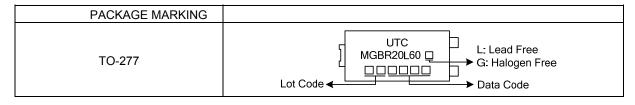
■ ORDERING INFORMATION

Ordering Number		Deslesses	Pin Assignment			Daabiaa	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MGBR20L60L-T27-R	MGBR20L60G-T27-R	TO-277	Α	K	Α	Tape Reel	

Note: Pin Assignment: A: Anode K: Common Cathode



■ MARKING INFORMATION



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TO-277

■ **ABSOLUTE MAXIMUM RATINGS**(T_A=25°C, unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER SYMBOL		RATINGS	UNIT
DC Blocking Voltage	V _{RM} 60		V
WorkingPeak Reverse Voltage	V _{RWM} 60		V
Peak Repetitive Reverse Voltage	V _{RRM} 60		V
Average Rectified Output Current T _C =140°C I	_o 20		Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load	I _{FSM} 250		Α
Repetitive Peak Avalanche Power (1µs, 25°C)	P _{ARM} 5	000	W
Operating Junction Temperature	T _J -65∼	+150	°C
Storage Temperature	T _{STG} -65	+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS (Note 3)

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θ_{JA}	73	°C/W	
Junction to Case	θ_{JC}	13	°C/W	

■ **ELECTRICAL CHARACTERISTICS**(T_A=25°C,unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	$V_{(BR)R}$	I _R =0.5mA 6	0			V
Forward Voltage Drop	VEM	I _F =20A, T _J =25°C			0.65	V
		I _F =20A, T _J =125°C			0.60	V
Lackage Compant (Nata 4)	I DM	V _R =60V, T _J =25°C		85	300	μΑ
Leakage Current (Note 1)		V _R =60V, T _J =125°C		12	40	mA

Notes: 1. Short duration pulse test used to minimize self-heating effect.

- 2. Thermal resistance junction to case mounted on heatsink.
- 3. Mounted on an FR4 PCB, single-sided copper, with 100 cm² copper pad area.

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